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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/728,909	12/08/2003	Сутиз Е. Tabery	H1124	9303	
75	90 08/26/2005		EXAM	EXAMINER	
	SNYDER, L.L.P.	GOUDREAU,	GOUDREAU, GEORGE A		
Suite 300 11240 Waples N	Mill Road		ART UNIT	PAPER NUMBER	
Fairfax, VA 2			1763		
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DATE MAILED: 08/26/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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•		Application No.	Applicant(s)	
		10/728,909	TABERY ET AL.	
	Office Action Summary	Examiner	Art Unit	
		George A. Goudreau	1763	
Pariod fo	The MAILING DATE of this communication	n appears on the cover sheet wit	h the correspondence addres	s
THE - Exte after - If the - If NO - Failt Any	ORTENED STATUTORY PERIOD FOR R MAILING DATE OF THIS COMMUNICATION of time may be available under the provisions of 37 CI SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, to period for reply is specified above, the maximum statutory pure to reply within the set or extended period for reply will, by the reply received by the Office later than three months after the led patent term adjustment. See 37 CFR 1.704(b).	ON. FR 1.136(a). In no event, however, may a re in. a reply within the statutory minimum of thirty eriod will apply and will expire SIX (6) MONT statute, cause the application to become AB/	ply be timely filed r (30) days will be considered timely. I'HS from the mailing date of this commul ANDONED (35 U.S.C. § 133).	· nication. ·
Status			•	
1)⊠	Responsive to communication(s) filed on	<u>29 April 2005</u> .		
2a)□	This action is FINAL . 2b)⊠	This action is non-final.		
3)	Since this application is in condition for all closed in accordance with the practice un			rits is
Disposit	ion of Claims	•	•	
5)□ 6)⊠ 7)⊠	Claim(s) <u>1-30</u> is/are pending in the applicated 4a) Of the above claim(s) <u>9-30</u> is/are with Claim(s) <u>is/are</u> allowed. Claim(s) <u>1,2,5 and 6</u> is/are rejected. Claim(s) <u>3,4,7 and 8</u> is/are objected to. Claim(s) <u>are subject to restriction and allowed.</u>	Irawn from consideration.		
Applicat	ion Papers			
9)[The specification is objected to by the Exa	miner.		
10)	The drawing(s) filed on is/are: a)	accepted or b) objected to b	y the Examiner.	
	Applicant may not request that any objection to	-,,	• •	
	Replacement drawing sheet(s) including the co	• • •		
11)[_]	The oath or declaration is objected to by the	ne Examiner. Note the attached	Office Action or form PTO-1	52.
Priority	under 35 U.S.C. § 119			
a)	Acknowledgment is made of a claim for for All b) Some * c) None of: 1. Certified copies of the priority docur 2. Certified copies of the priority docur 3. Copies of the certified copies of the application from the International Besee the attached detailed Office action for a	ments have been received. ments have been received in Appriority documents have been ureau (PCT Rule 17.2(a)).	oplication No received in this National Stag	je † Gonuên DREAU
Ass t-			PRIMARY EXAI	SI
Attachmer	• •	4) ☐ Internite C	immary (BTO 412)	ノ
	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-94)		ummary (PTO-413))/Mail Date	
3) 🛭 Infor	mation Disclosure Statement(s) (PTO-1449 or PTO/S er No(s)/Mail Date		formal Patent Application (PTO-152)

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1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- Claims 1-2, and 5-6 are rejected under 35 U.S.C. 102(b) as being anticipated by Keno et. al. (JP 08-236,475).
 - Keno et. al. disclose a process for forming a bump contact in a MOS semiconductor device which is comprised of the following steps:
 - -A multi-layer laminate which is comprised of SiO2 (11)/ polysi (12)/ Si3N4 (13) is formed onto the surface of a cz-Si wafer (10).;
 - -A patterned photo resist etch mask is formed onto the surface of the Si3N4 film.;
 - -The Si3N4 anti-reflective film (13) is etched using the patterned photo resist etch mask.:
 - -The photo resist etch mask is removed from the surface of the wafer.;
 - -The patterned Si3N4 mask is used in the selective thermal oxidation of the exposed regions of the polysi film (12) to form a SiO2 film (14).;
 - -The exposed region of the SiO2 films (11, 14) are etched using the patterned Si3N4 film as an etch mask.;
 - -The Si3N4 etch mask is removed from the surface of the wafer.; and
 - -A W contact (17) is formed in the contact window (16), which contacts the surface of the Si wafer.

This is discussed specifically in the abstract; and discussed in general in

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columns 1-8. This is shown specifically in figure 1; and shown in general in figures 1-5.

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3. Claims 3-4, and 7-8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

- 4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- 5. Any inquiry concerning this communication should be directed to examiner George A. Goudreau at telephone number (571)-272-1434.

George A. Goudreau

Primary Examiner

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